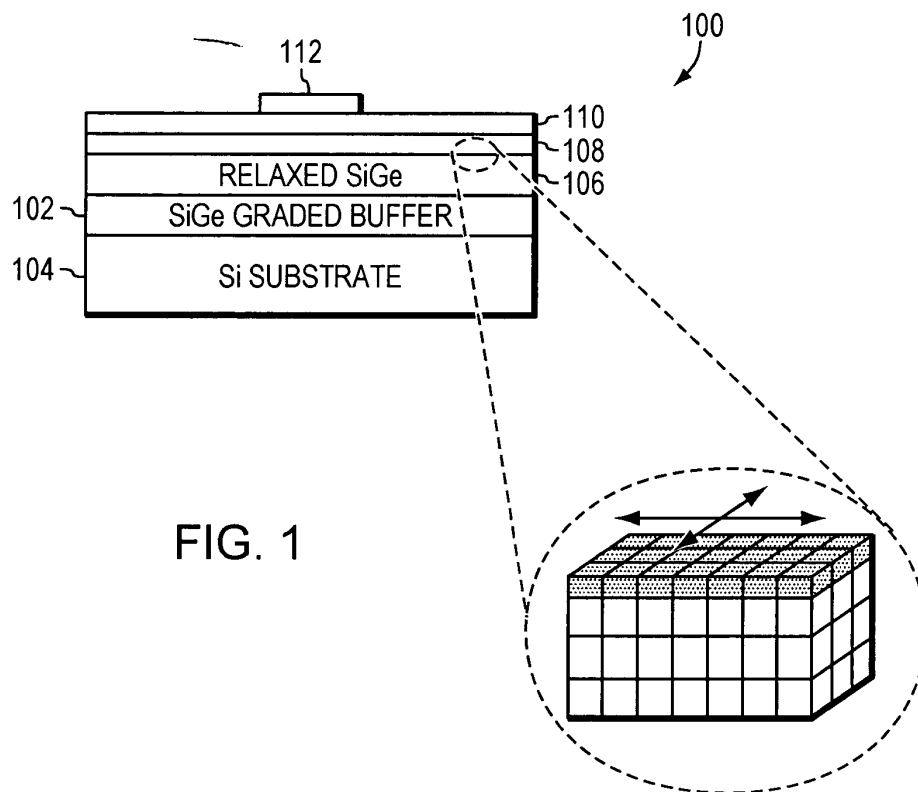




Title: METHOD OF FABRICATING CMOS INVERTER  
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SILICON SURFACE CHANNEL MOSFETS  
Inventors: Fitzgerald *et al.* (Serial No. 09/884,172)  
Express Mail Label No. EV192308481US  
Atty Docket No.: ASC-044  
Attorney for Applicants: Natasha C. Us

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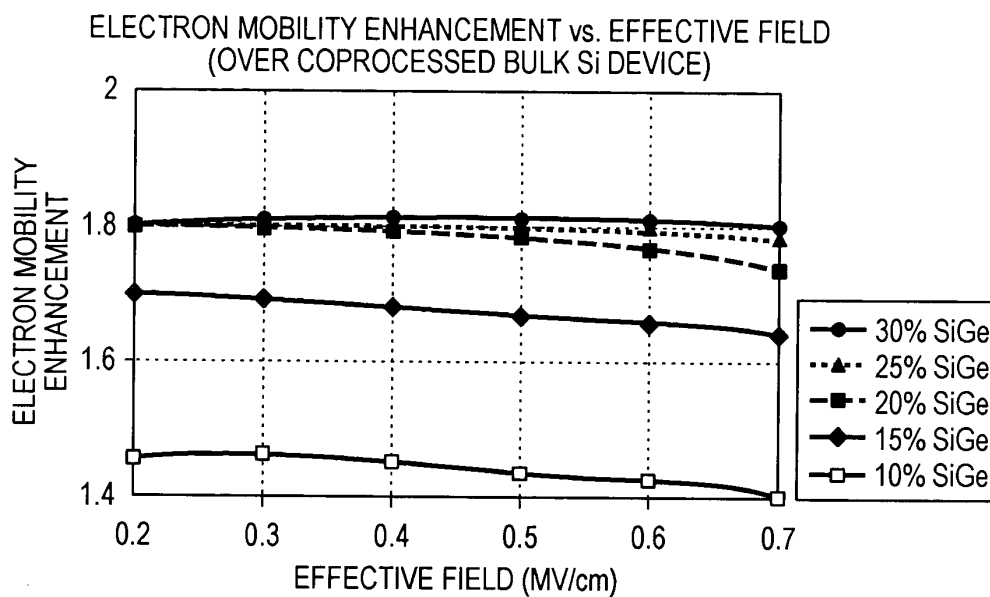


FIG. 2A

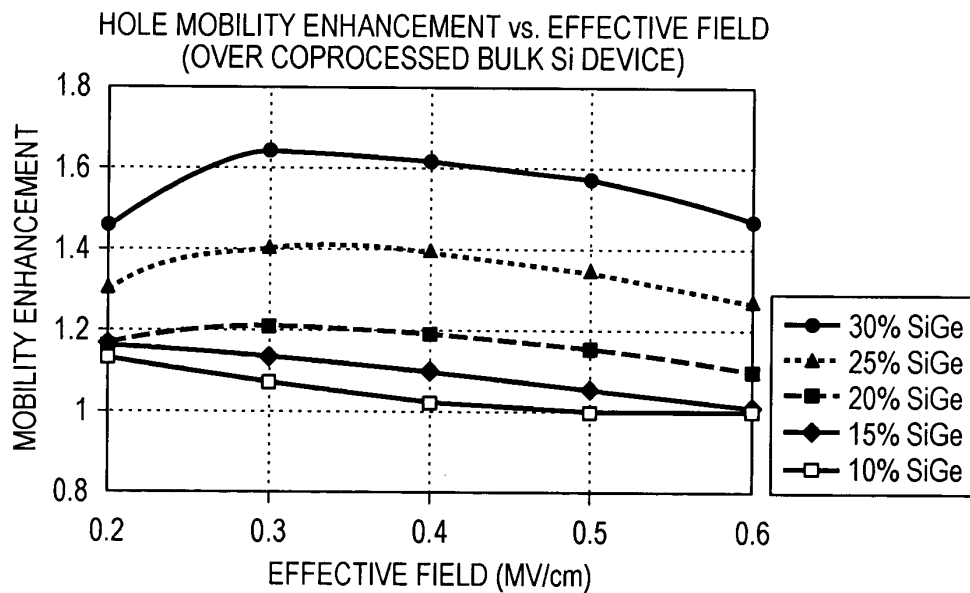
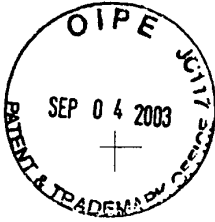


FIG. 2B



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TYPE OF SURFACE	AVERAGE ROUGHNESS (nm)
AS-GROWN GRADED COMPOSITION RELAXED SiGe	7.9
PLANARIZED SiGe	0.57
REGROWTH SiGe	-0.6

FIG. 3





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Attorney for Applicants: Natasha C. Us

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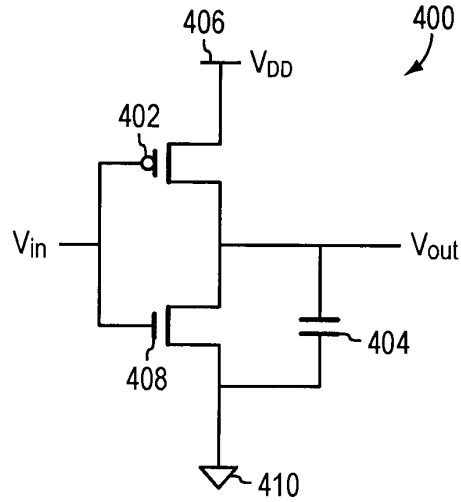


FIG. 4





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Atty Docket No.: ASC-044  
Attorney for Applicants: Natasha C. Us

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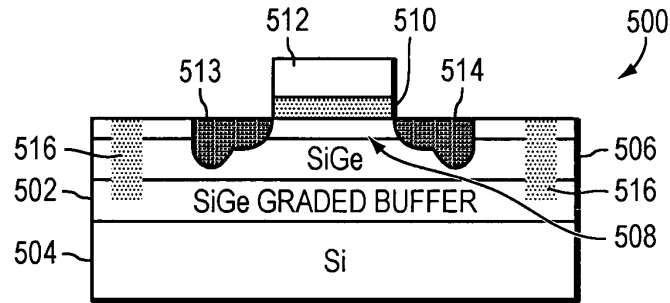


FIG. 5A

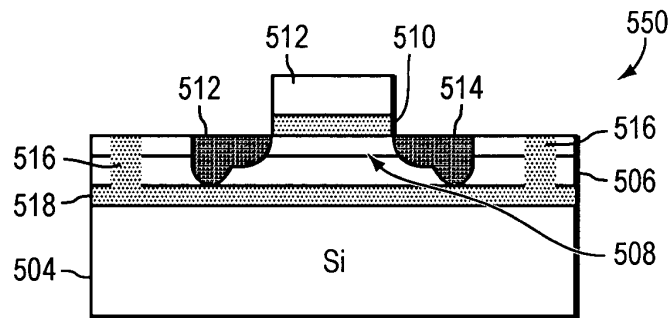


FIG. 5B





Title: METHOD OF FABRICATING CMOS INVERTER  
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	n ENHANCEMENT	p ENHANCEMENT
$\text{Si}_{0.8}\text{Ge}_{0.2}$	1.75	1
$\text{Si}_{0.7}\text{Ge}_{0.3}$	1.8	1.4

FIG. 6





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	BULK SILICON	STRAINED-Si ON 20% SiGe: HIGH SPEED	STRAINED-Si ON 30% SiGe: HIGH SPEED	STRAINED-Si ON 20% SiGe: LOW POWER	STRAINED-Si ON 30% SiGe: LOW POWER
n ENHANCEMENT	1	1.75	1.8	1.75	1.8
p ENHANCEMENT	1	1	1.4	1	1.4
$W_p$ ( $\mu\text{m}$ )	5.4	5.4	5.4	5.4	5.4
$W_n$ ( $\mu\text{m}$ )	1.8	1.8	1.8	1.8	1.8
$L_n, L_p$ ( $\mu\text{m}$ )	1.2	1.2	1.2	1.2	1.2
$C_L$ (fF)	32	32	32	32	32
$V_{DD}$ (V)	5	4.7	4.4	4.3	3.8
$NM_H$ (V)	2.053	2.218	1.949	2.037	1.682
$NM_L$ (V)	2.067	1.654	1.721	1.542	1.504
$t_{pHL}$ (psec)	211.3	133.7	141.6	152.2	180.1
$t_{pLH}$ (psec)	195.8	220.0	173.3	254.8	226.9
$t_p$ (psec)	203.5	176.9	157.4	203.5	203.5
POWER (mW)	3.93	3.93	3.93	2.87	2.21
% SPEED INCREASE	-	15.1%	29.3%	-	-
% POWER REDUCTION	-	-	-	27.0%	43.7%

FIG. 7

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	BULK SILICON	STRAINED-Si ON 20% SiGe: CONSTANT $V_{DD}$	STRAINED-Si ON 30% SiGe: CONSTANT $V_{DD}$	STRAINED-Si ON 20% SiGe: HIGH SPEED SYMMETRICAL INVERTER	STRAINED-Si ON 30% SiGe: HIGH SPEED SYMMETRICAL INVERTER	STRAINED-Si ON 20% SiGe: LOW POWER SYMMETRICAL INVERTER	STRAINED-Si ON 30% SiGe: LOW POWER SYMMETRICAL INVERTER
n ENHANCEMENT	1	1.75	1.8	1.75	1.8	1.75	1.8
p ENHANCEMENT	1	1	1.4	1	1.4	1	1.4
$W_p$ ( $\mu m$ )	5.4	5.4	5.4	9.45	6.94	9.45	6.94
$W_n$ ( $\mu m$ )	1.8	1.8	1.8	1.8	1.8	1.8	1.8
$L_n, L_p$ ( $\mu m$ )	1.2	1.2	1.2	1.2	1.2	1.2	1.2
$C_L$ (fF)	32	32	32	32	32	32	32
$V_{DD}$ (V)	5	5	5	4.3	4.2	3.5	3.5
$NM_H$ (V)	2.053	2.376	2.198	1.782	1.770	1.5018	1.4796
$NM_L$ (V)	2.067	1.751	1.923	1.794	1.781	1.5101	1.4876
$t_{pHL}$ (psec)	211.3	120.7	117.4	152.0	149.5	204.4	204.1
$t_{pLH}$ (psec)	195.8	195.8	139.9	145.4	143.3	202.6	202.9
$t_p$ (psec)	203.5	158.3	128.6	148.7	146.4	203.5	203.5
POWER (mW)	3.93	5.06	6.22	3.93	3.93	1.95	1.89
% SPEED INCREASE	-	28.6%	58.3%	36.9%	39.0%	-	-
% POWER REDUCTION	-	-	-	-	-	50.4%	52.0%

FIG. 8





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	BULK SILICON	STRAINED-Si ON 20% SiGe: HIGH SPEED	STRAINED-Si ON 30% SiGe: HIGH SPEED	STRAINED-Si ON 20% SiGe: LOW POWER	STRAINED-Si ON 30% SiGe: LOW POWER
n ENHANCEMENT	1	1.75	1.8	1.75	1.8
p ENHANCEMENT	1	1	1.4	1	1.4
W <sub>p</sub> (μm)	3.11	4.12	3.53	4.12	3.53
W <sub>n</sub> (μm)	1.8	1.8	1.8	1.8	1.8
L <sub>n</sub> , L <sub>p</sub> (μm)	1.2	1.2	1.2	1.2	1.2
C <sub>L</sub> (fF)	22.5	26.7	24.2	26.7	24.2
V <sub>DD</sub> (V)	5	4.5	4.3	4.4	3.8
NM <sub>H</sub> (V)	2.370	2.275	2.123	2.220	1.872
NM <sub>L</sub> (V)	1.756	1.485	1.511	1.458	1.371
t <sub>pHL</sub> (psec)	148.4	117.3	109.3	121.5	132.4
t <sub>pLH</sub> (psec)	238.5	254.8	204.9	265.3	254.4
t <sub>p</sub> (psec)	193.4	186.0	157.1	193.4	193.4
POWER (mW)	2.90	2.90	2.90	2.66	1.83
% SPEED INCREASE	-	4.0%	23.1%	-	-
% POWER REDUCTION	-	-	-	8.4%	37.1%

FIG. 9





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Attorney for Applicants: Natasha C. Us

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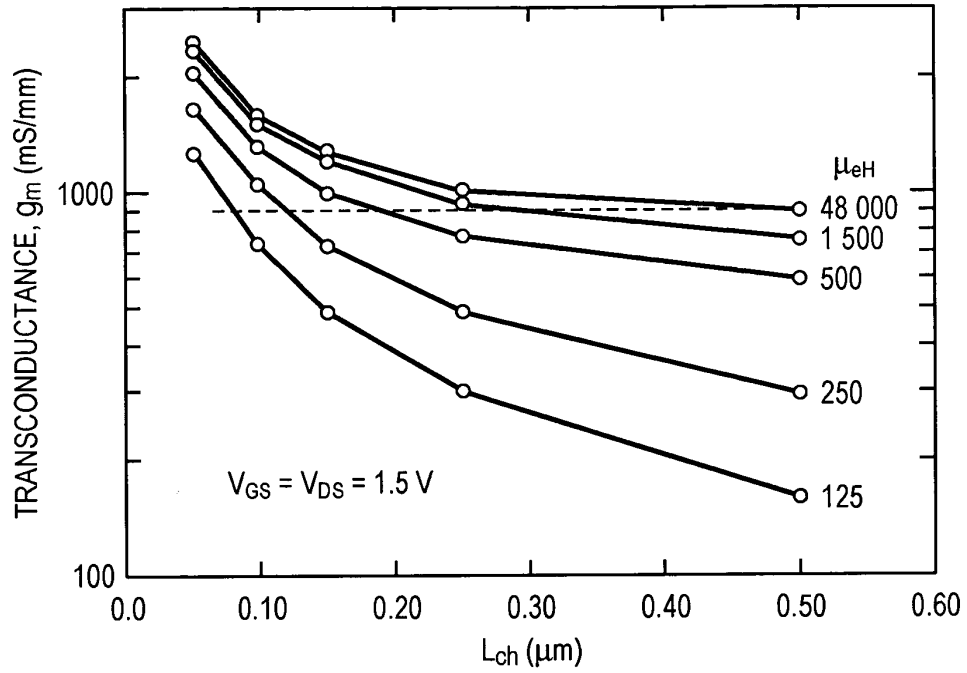


FIG. 10





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Atty Docket No.: ASC-044  
Attorney for Applicants: Natasha C. Us

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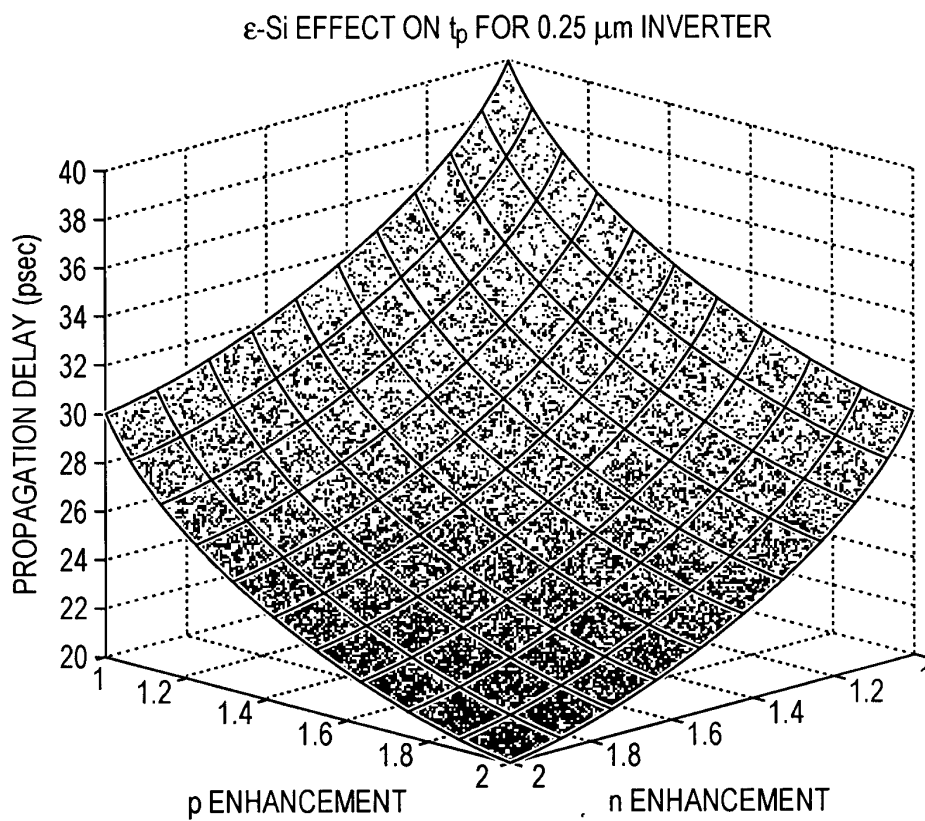
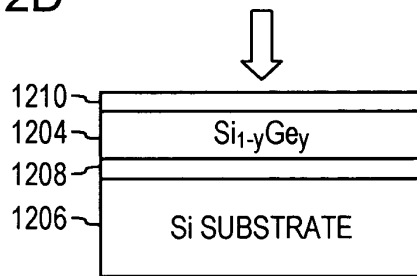
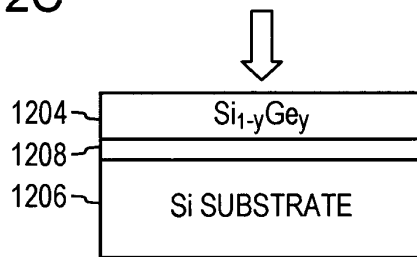
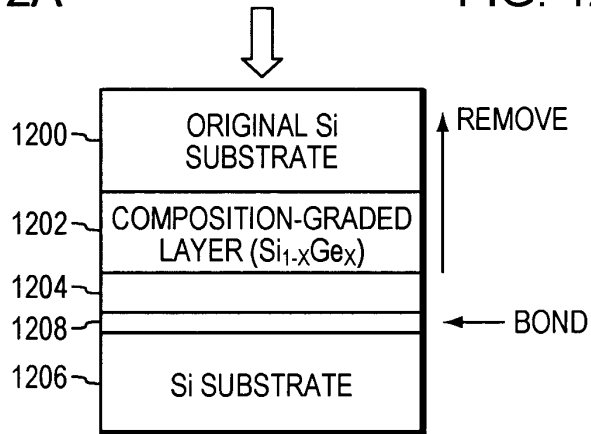
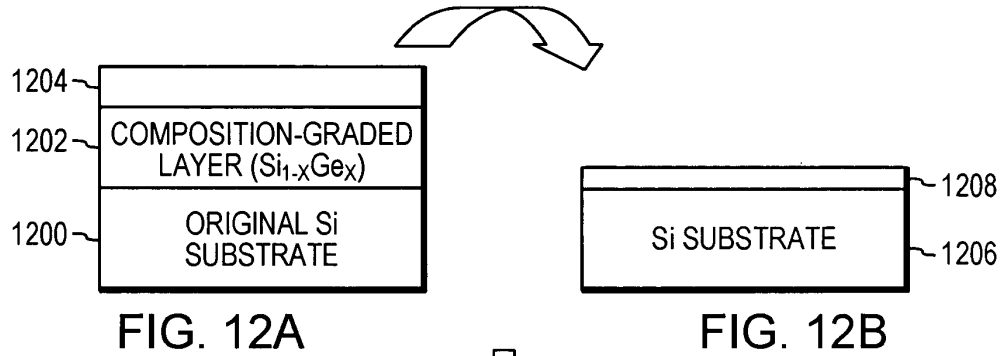


FIG. 11





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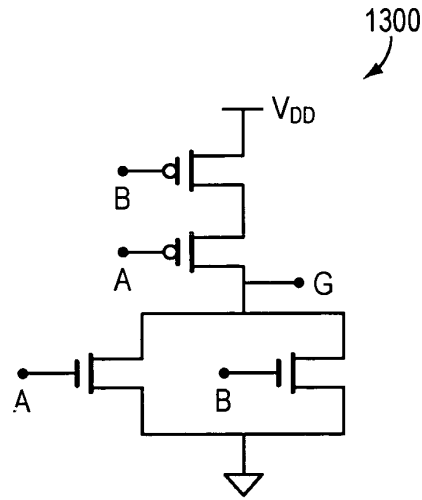


FIG. 13A

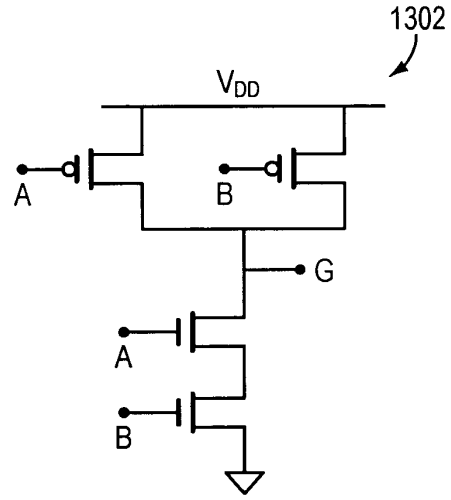


FIG. 13B

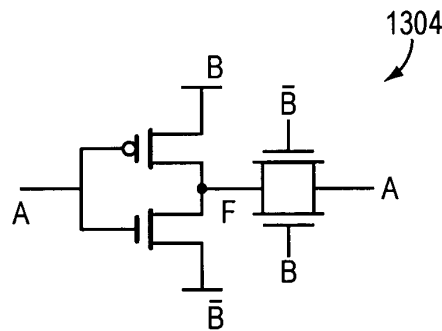


FIG. 13C